

38. (Canceled)

39. (Previously Presented) The electronic fuse of Claim 37, wherein said nonvolatile memory element comprises a floating-gate transistor having a floating gate, an amount of charge on the floating gate determining said memory value.

*TP* 40. (Original) The electronic fuse of Claim ~~38~~<sup>39 34</sup>, wherein said nonvolatile memory element comprises a nonvolatile memory element manufactured in a MOS fabrication process.

41. (Original) The electronic fuse of Claim 39, wherein said floating-gate transistor is a MOS device.

42. (Canceled)

43. (Original) The electronic fuse of Claim 39, wherein the amount of charge on the floating gate may be changed using Fowler-Nordheim tunneling.

44. (Original) The electronic fuse of Claim 39, wherein the amount of charge on the floating gate may be changed using hot-electron injection.

45. (Original) The electronic fuse of Claim 39, wherein the amount of charge on the floating gate may be changed using direct tunneling.

46. (Original) The electronic fuse of Claim 39, wherein the amount of charge on the floating gate may be changed using hot-hole injection.

47. (Canceled)